

RB521S-30

SILICON EPITAXIAL PLANAR SCHOTTKY BARRIER DIODE

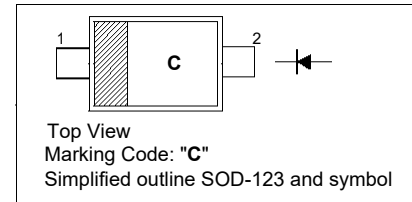
for low current rectification and high speed switching applications

Features

- Extremely small surface mounting type

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Absolute Maximum Ratings (T_a = 25°C)

Parameter	Symbol	Value	Unit
Reverse Voltage	V _R	30	V
Mean Rectifying Current	I _o	200	mA
Peak Forward Surge Current (60Hz for Cyc.)	I _{FSM}	1	A
Junction Temperature	T _j	125	°C
Storage Temperature Range	T _{stg}	- 40 to + 125	°C

Characteristics at T_a = 25°C

Parameter	Symbol	Value	Unit
Forward Voltage at I _F = 200 mA	V _F	0.5	V
Reverse Current at V _R = 10 V	I _R	30	μA

⌘Electrical characteristic curves (T_a=25° C)

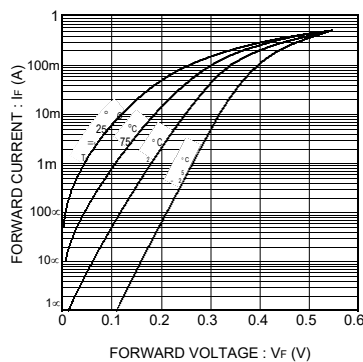


Fig. 1 Forward characteristics

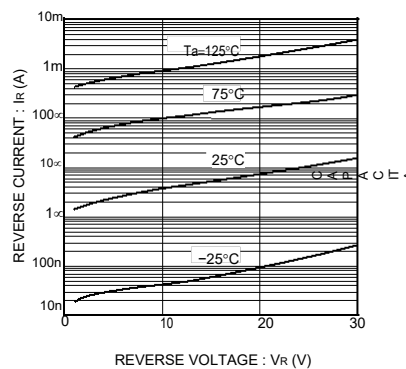


Fig. 2 Reverse characteristics

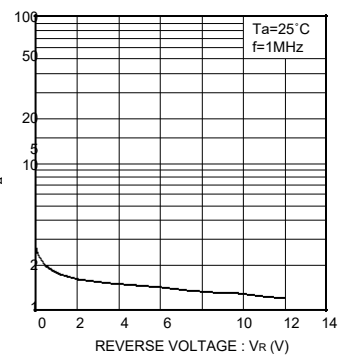
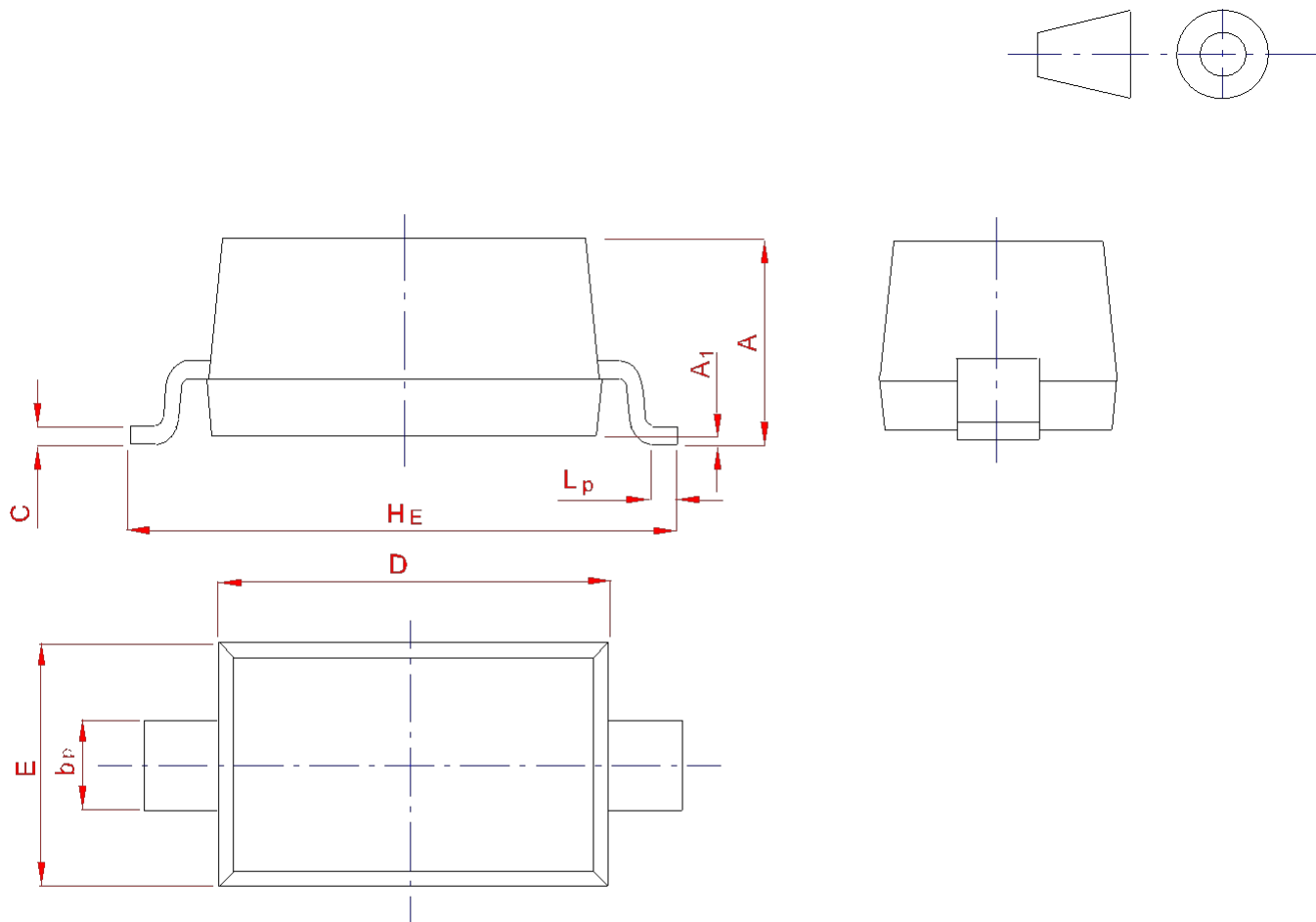


Fig. 3 Capacitance between terminals characteristics

PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-123



UNIT	A	bp	C	D	E	HE	A1	Lp
mm	1.20	0.60	0.135	2.75	1.65	3.85	0.10	0.50
	0.90	0.50	0.100	2.55	1.55	3.55	0.01	0.20